

PMBT2222; PMBT2222A

FEATURES

- High current (max. 600 mA)
- Low voltage (max. 40 V).

APPLICATIONS

- Switching and linear amplification.

DESCRIPTION

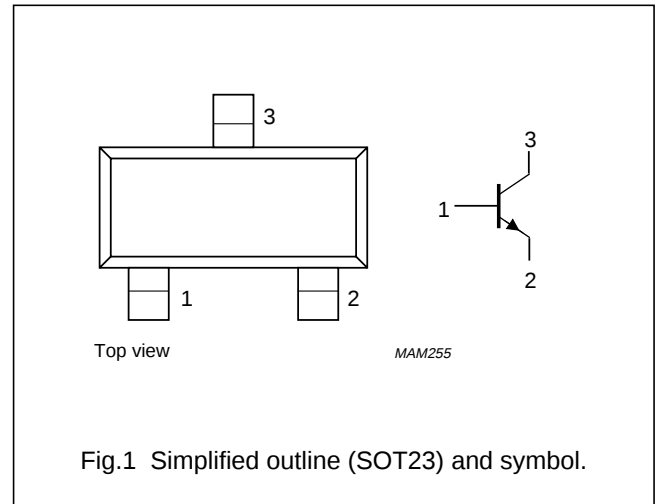
NPN switching transistor in a SOT23 plastic package.
PNP complements: PMBT2907 and PMBT2907A.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PMBT2222	*1B
PMBT2222A	*1P

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter			
	PMBT2222		–	60	V
	PMBT2222A		–	75	V
V_{CEO}	collector-emitter voltage	open base			
	PMBT2222		–	30	V
	PMBT2222A		–	40	V
V_{EBO}	emitter-base voltage	open collector			
	PMBT2222		–	5	V
	PMBT2222A		–	6	V
I_C	collector current (DC)		–	600	mA
I_{CM}	peak collector current		–	800	mA
I_{BM}	peak base current		–	200	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Note

1. Transistor mounted on an FR4 printed-circuit board.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

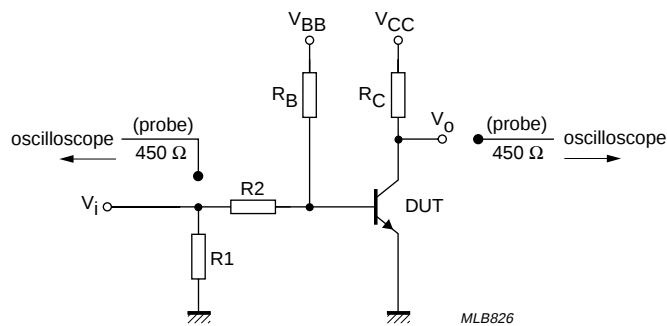
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{CBO}	collector cut-off current PMBT2222	$I_E = 0; V_{CB} = 50\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 50\text{ V}; T_j = 125\text{ °C}$	–	10	μA
	collector cut-off current PMBT2222A	$I_E = 0; V_{CB} = 60\text{ V}$	–	10	nA
		$I_E = 0; V_{CB} = 60\text{ V}; T_j = 125\text{ °C}$	–	10	μA
I_{EBO}	emitter cut-off current PMBT2222A	$I_C = 0; V_{EB} = 5\text{ V}$	–	10	nA
h_{FE}	DC current gain	$I_C = 0.1\text{ mA}; V_{CE} = 10\text{ V}$	35	–	
		$I_C = 1\text{ mA}; V_{CE} = 10\text{ V}$	50	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}$	75	–	
		$I_C = 10\text{ mA}; V_{CE} = 10\text{ V}; T_{amb} = -55\text{ °C}$	35	–	
		$I_C = 150\text{ mA}; V_{CE} = 10\text{ V}$	100	300	
		$I_C = 150\text{ mA}; V_{CE} = 1\text{ V}$	50	–	
	DC current gain PMBT2222 PMBT2222A	$I_C = 500\text{ mA}; V_{CE} = 10\text{ V}$	30	–	
			40	–	
V_{CEsat}	collector-emitter saturation voltage PMBT2222 PMBT2222A	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	400	mV
			–	300	mV
	collector-emitter saturation voltage PMBT2222 PMBT2222A	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	1.6	V
			–	1	V
V_{BEsat}	base-emitter saturation voltage PMBT2222 PMBT2222A	$I_C = 150\text{ mA}; I_B = 15\text{ mA}; \text{note 1}$	–	1.3	V
			0.6	1.2	V
	base-emitter saturation voltage PMBT2222 PMBT2222A	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	2.6	V
			–	2	V
C_c	collector capacitance	$I_E = I_E = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$	–	8	pF

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SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
C_e	emitter capacitance PMBT2222 PMBT2222A	$I_C = I_C = 0$; $V_{EB} = 500$ mV; $f = 1$ MHz	– –	30 25	
f_T	transition frequency PMBT2222 PMBT2222A	$I_C = 20$ mA; $V_{CE} = 20$ V; $f = 100$ MHz	250 300	– –	MHz MHz
F	noise figure	$I_C = 100$ μ A; $V_{CE} = 5$ V; $R_S = 1$ k Ω ; $f = 1$ kHz	–	4	dB
Switching times (between 10% and 90% levels); (see Fig.2)					
t_{on}	turn-on time	$I_{Con} = 150$ mA; $I_{Bon} = 15$ mA; $I_{Boff} = -15$ mA	–	35	ns
t_d	delay time		–	15	ns
t_r	rise time		–	20	ns
t_{off}	turn-off time		–	250	ns
t_s	storage time		–	200	ns
t_f	fall time		–	60	ns

Note

1. Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.



$V_i = 9.5$ V; $T = 500$ μ s; $t_p = 10$ μ s; $t_r = t_f \leq 3$ ns.
 $R_1 = 68$ Ω ; $R_2 = 325$ Ω ; $R_B = 325$ Ω ; $R_C = 160$ Ω .
 $V_{BB} = -3.5$ V; $V_{CC} = 29.5$ V.
 Oscilloscope: input impedance $Z_i = 50$ Ω .

Fig.2 Test circuit for switching times.